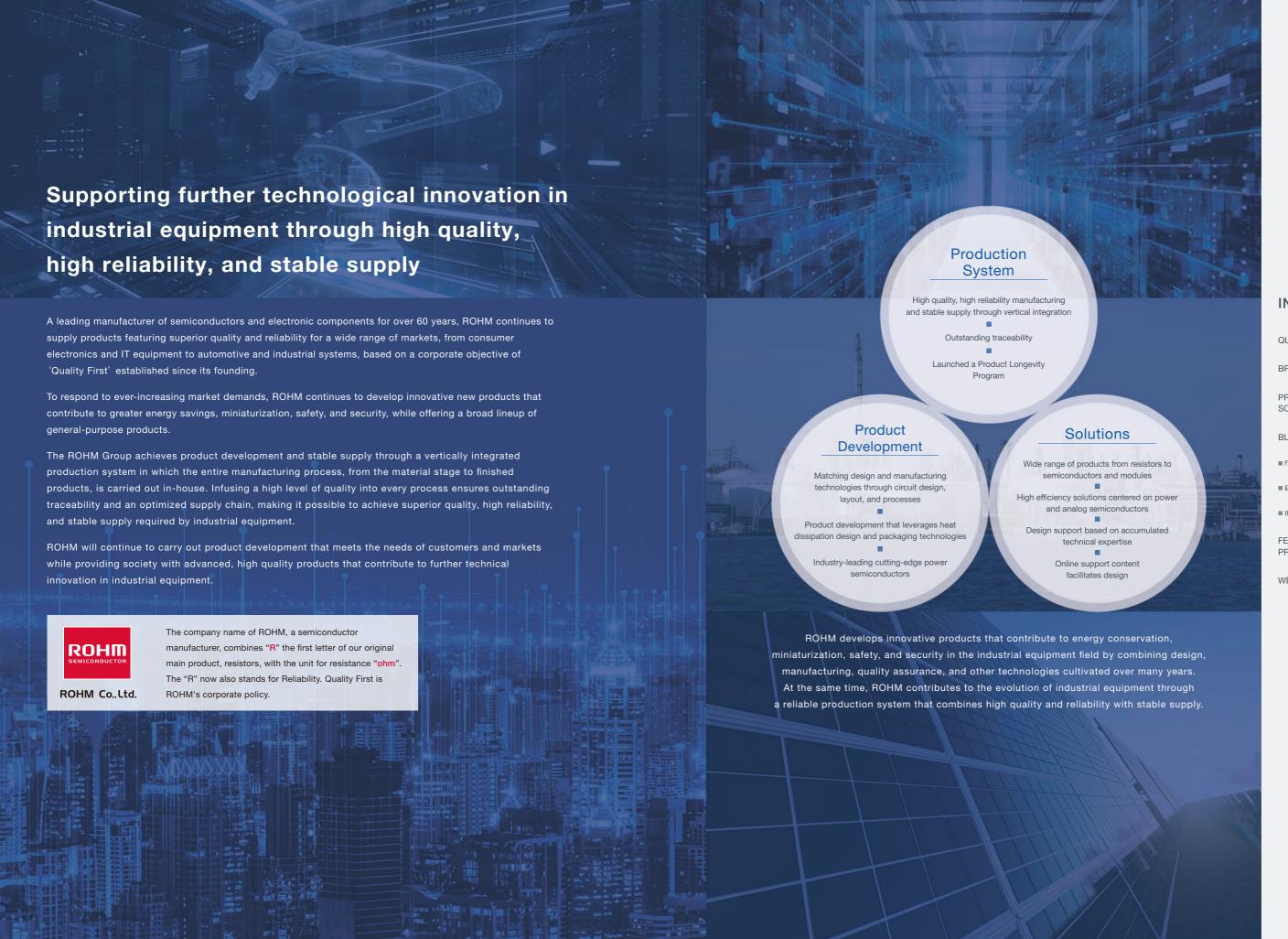


Application Brochure for

INDUSTRIAL

Ver.3.1





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QUALITY

Achieving high quality and stable supply through a vertically integrated production system

ROHM pursues 'quality first' manufacturing.

To guarantee consistent quality assurance and stable supply, the ROHM Group has established a vertically integrated production system in which the entire manufacturing process, from the material stage to finished products, is completed in-house, together with a BCM (Business Continuity Management) system that can maintain product supply even in the event of unforeseen circumstances such as natural disasters. The result is a business model that is less susceptible to the effects of natural and man-made disasters compared to general fabless and foundry, ensuring stable supply to customers around the world.

What's more, ROHM products achieve 4M traceability (Man, Machine, Material, Method) in all processes by allowing production information (production data/lot data) to be obtained from the actual items.

Special Attention on Raw Materials Wafer production from silicon ingot pulling Silicon Ingot



In-house Photo Mask

Pursuing high quality through integrated quality control, from IC chip design layout to photo mask production





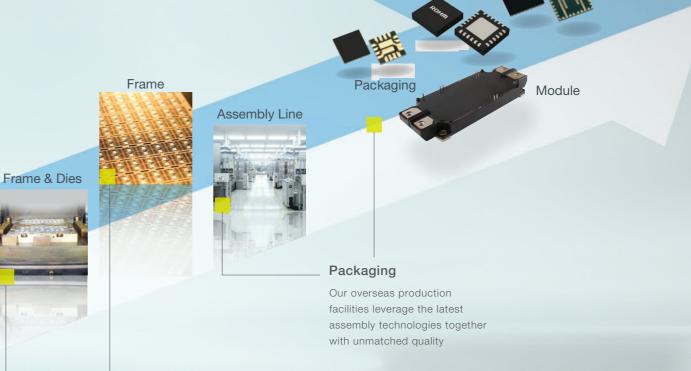
Wafer Process

facilities in Japan

Innovative device development from the wafer process,

centered on our production

In-house Dies and Lead Frames To provide high quality, some lead frames and molds are produced in-house to help control the quality of outsourced products and ensure stable supply



through complete automation.

Flexible Lines ROHM utilizes state-of-the-art production lines that minimize quality fluctuation factors by reducing human intervention



SiCrystal

SiC Single-crystal Wafer Manufacturer

SiCrystal, a German SiC single-crystal wafer manufacturer, became a member of the ROHM Group in 2009

In April 2021, ROHM launched operations of flexible lines that automate the assembly process utilizing in-house technologies with the goal of labor savings and high-mix low-volume production. These flexible lines improve product quality by increasing the capability of processes themselves based on FMEA (Failure Mode Effects Analysis) while doubling productivity, reducing manpower by automating everything from production instructions, material/product transport and supply to tool changes and record keeping. In addition, by implementing process design from the planning stage, lead time has been reduced by 10x vs conventional. Going forward, ROHM plans on applying this flexible line technology to mass production lines to achieve even more stable supply and strengthen our BCM system.

03 ROHM Application Brochure for INDUSTRIAL ROHM Application Brochure for INDUSTRIAL 04

BROAD MARKET



PRODUCT and SOLUTION

Offering optimized solutions through a broad product lineup

ROHM's wide range of products from resistors to semiconductor components, ICs, and modules makes it possible to propose solutions at the system level for industrial equipment and other fields.

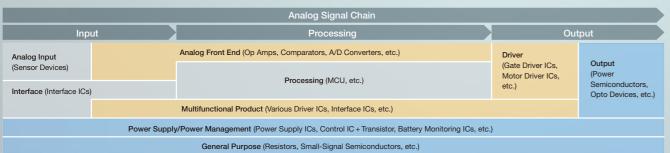
The ROHM Group's considerable capabilities allow us to deliver solutions tailored to application needs.







ROHM's Product Portfolio



ROHM develops products featuring excellent performance by combining circuit design, layout, and manufacturing process technologies.

Nano Pulse Control™ **■**

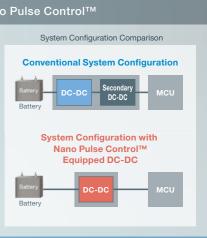


Ultra-high-speed pulse control technology achieves circuit control with switching ON times (control pulse width of the power supply IC) on the order of nanoseconds. Power supply ICs incorporating this technology enable high to low voltage conversion using a single IC - unlike conventional solutions requiring 2 or more power supply ICs. This is also being developed as a useful technology for driving GaN devices that excel at high frequency operation.



Nano Pulse Control™ is a trademark or registered trademark of ROHM Co., Ltd.

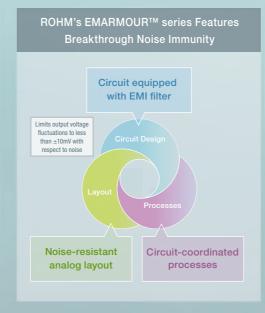
Effects of Nano Pulse Control™ Control Pulse Width Comparison



Ultra-fast control in the high frequency range contributes to smaller, simpler systems

A brand name given only to products that achieve noise immunity limiting output voltage fluctuations to less than ±300mV over the entire noise frequency band during international noise evaluation testing under the ISO11452-2 standard. Unprecedented noise immunity both reduces design load while improving reliability by solving issues related to noise in the development of a variety of systems.





Noise suppression in ires difficult using an input filter alone A test in which noise is applied to the wiring harness connected to an electronic device using a current injection probe. The immunity of electronic devices is evaluated when excited by strong magnetic field noise A test being increasingly adopted by electronics manufacturers due to the proliferation of mobile phones Electromagnetic radiation from the antenna makes countermeasures difficult using an input filter alone Countermeasures are relatively easy, such as installing a filter at the input terminal in advance

High EMI Immunity Op Amp Development Concept

Achieves unparalleled performance in 4 international noise tests

ROHM's New EMARMOUR™ Op Amp series

EMARMOUR™ is a trademark or registered trademark of ROHM Co., Ltd.

07 ROHM Application Brochure for INDUSTRIAL

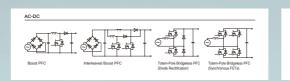
PRODUCT and SOLUTION

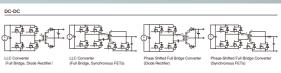
Design support in line with the customer's development stage

Design support content that helps solve issues at all stages of customer development is available for immediate access on ROHM's website. ROHM provides solutions that can be used in customer circuit designing, such as content for each product required when designing industrial equipment, and application circuits with drive ICs that maximize the performance of power semiconductors.



Optimized Device Proposals Based on Circuit Configuration [Topology Selection]





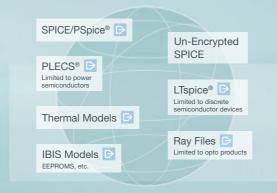
Topology Selection presents the devices most suitable for the circuit configuration (topology) used in the customer's application. Referencing the combination of devices that make up the circuit reduces the number of resources required for component selection.



Evaluated Design Data [Reference Design]

A Reference Design is design data that has been evaluated at the circuit level for the application. Circuit schematics, Bill of Materials (BOM), evaluation data, and board Gerber data are available for easy design reuse Some boards are also available for sale, eliminating the need to develop boards for actual device verification.





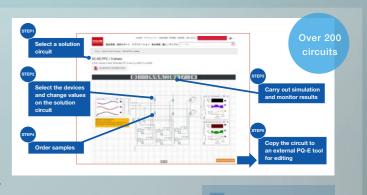
Multiple Design Models for **Different Tools and Applications**

Various design models including thermal models, PLECS models, and Ray files are available for thermal, optical, and electronic circuit simulations. Usage is supported by application notes.

Spice® is a registered trademark of Cadence Design Systems, Inc. LTSpice® is a registered trademark of Analog Devices, Inc. PLECS® is a registered

ROHM Solution Simulator Enables Batch Verification of Power Semiconductors and Various ICs

ROHM Solution Simulator is a free electronic circuit simulator hosted on ROHM's website. A wide range of applications is supported, from initial studies to system-level operation verification. ROHM power semiconductors, gate drivers, power supply ICs, and passive components (e.g. shunt resistors) can be easily and accurately verified together in a solution circuit close to actual user conditions.



ROHM Solution Simulat

FACTORY AUTOMATION

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AC SERVO

INVERTER

ENERGY

BMS

SOLAR INVERTER

AC-DC CONVERTER

INFRASTRUCTURE

SURVEILLANCE CAMERA P.24

BASE STATION

SERVER BOARD

GAS LEAK ALARM

xEV CHARGING STATION P.20

AGV

PLC

Devices and solutions that

support greater energy savings,

higher speeds, and increased

Factory Automation equipment

miniaturization required by

Optimized devices for

the system ensure efficient

use of power without waste

Configuring high reliability

applications for safer,

more secure lifestyles

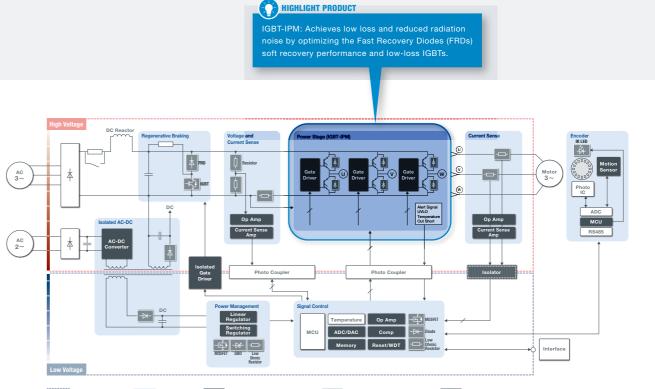


AC Servos: 3-Phase AC100V to 240V Motor Drive

AC servos require not only high power and controllability, but greater miniaturization as well.

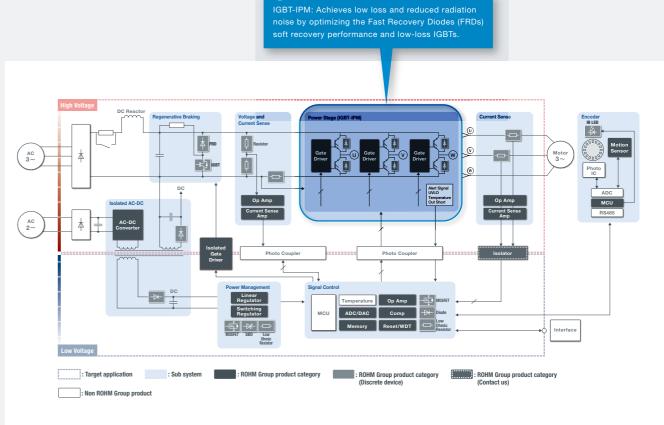
ROHM offers a lineup of IGBT-IPM that integrate power semiconductors and drive ICs optimized for motor drive in a single package,

ROHM also provides accelerometers for monitoring that contribute to greater energy savings, miniaturization, and safety.





along with a variety of power management ICs for power supply systems.





PRODUCT

Power Stage () IGBT-IPM □ IGBT 🗈

Regeneration Braking

IGBT 🗈

Fast Recovery Diodes D **Gate Driver**

Isolated Gate Drivers D IGBT/MOSFET High/Low Side Gate Drivers **□**

Voltage and Current Sense

Current Detection Resistors Current Sense Amplifiers Low Offset OpAmps D High Voltage Resistors D

Isolated AC-DC

AC-DC Converters Schottky Barrier Diodes 🗈

Encoder 16bit MCU 🗈

Accelerometers D IR LEDs 🗈

Power Management Switching Regulators D

Linear Regulators D Schottky Barrier Diodes MOSFETs 🗈 Resistors 🗈

Signal Control/General Purpose

D/A Converters EEPROMs 🗈 MOSFETs 🗈 Operational Amplifiers 🗈 Diodes 🗈 Comparators D **Current Detection** RESET ICs 🗈 A/D Converters D Resistors 🗈

- 3Phase AC400V Inverter D
- = Single Phase AC100V-240V no ■ DC12V-48V Industry D

■ New 600V IGBT-IPMs Deliver Class-Leading Low Noise with Low Loss

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INFRASTRUCTURE

BLOCK DIAGRAM

FACTORY AUTOMATION

INVERTER

Inverters: 3-Phase AC400V Motor Drive

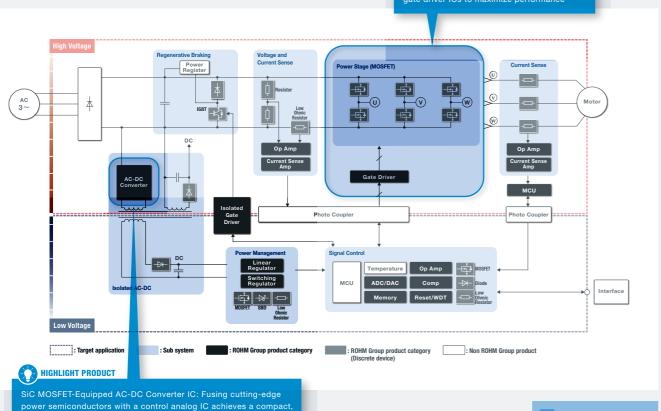
Inverters require high power high efficiency operation to drive large current motors without waste.

ROHM provides power solutions for motor drive that incorporate state-of-the-art power semiconductors centered on SiC MOSFETs,

high performance magnetically isolated gate driver ICs, and high accuracy shunt resistors. Also offered is a broad lineup of power

supply ICs for auxiliary power supplies along with system-level solution proposals that contribute to high efficiency operation and improved reliability.

HIGHLIGHT PRODUCT SiC MOSFETs/Gate Driver IC: Power solutions include industry-leading SiC MOSFETs and gate driver ICs to maximize performance



PRODUCT

Power Stage

SiC 🗈 IGBT 🗈 Regeneration Braking

nigh efficiency auxiliary power supply

Fast Recovery Diodes **Gate Driver**

solated Gate Drivers IGBT/MOSFET High/Low Side Gate Drivers

Isolated AC-DC

Schottky Barrier Diodes

Voltage and Current Sense

Current Detection Resistors D Current Sense Amplifiers D Low Offset Op Amps D High Voltage Resistors D

Power Management Switching Regulators Linear Regulators Schottky Barrier Diodes D

MOSFETs D Resistors 🗈

Signal Control/General Purpose

EEPROMs 🗈 Operational Amplifiers D Comparators D RESET ICs 🗈 A/D Converters

D/A Converters MOSFETs 🗈 Diodes 🗈

Current Detection Resistors Resistors 🗈

■ Single Phase AC100V-240V non–Isolated 🖸

- DC12V-48V Industry 🕒
- 3Phase AC100V-240V AC Servo 🕞

ROHM's Industry-first* AC-DC Converter ICs of Surface Mount Package with Built-In 1700V SiC MOSFET [5]

5kW High Efficiency Fan-less Inverter Circuit Reference Design with SiC MOSFETs [REFPDT007]

The REFPDT007 utilizes a transformer-link interleaved circuit in the inverter block that takes advantage of the high-frequency switching performance of SiC MOSFETs to achieve a power conversion efficiency of 99% or higher at 5kW. SiC MOSFETs (SCT3017AL, SCT3030AL) are implemented in a novel circuit topology that delivers high efficiency by reducing winding reactance and copper losses. High 99% efficiency (51W) operation that suppresses heat generation enables cooling using just small heat dissipation fins without the need for a cooling fan. What's more, the interleaved design doubles the apparent switching frequency, while miniaturization of the smoothing filter halves the size and weight compared to conventional full-bridge types.

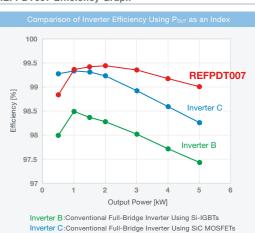
Specifications

Reference Board Part No.	REFPDT007-EVK-001
V_{IN}	DC320V
V _{out}	AC200V
I _{OUT}	AC25A
f _{sw}	40kHz
I _{OUT pp} /I _{OUT peak}	Less than 0.2
Bm Max	Less than 0.15T

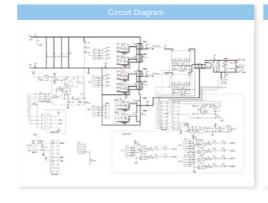
*This reference board consists of three boards

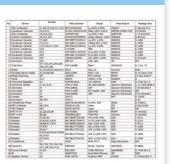
Reference Board Part No.	Туре
REFPDT007-EVK-001A	Power Stage
REFPDT007-EVK-001B	Controller Board
REFPDT007-EVK-001C	Aux Power Supply

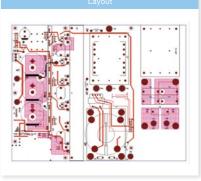
REFPDT007 Efficiency Graph



Design Data e.g.:REFPDT007-EVK-001A









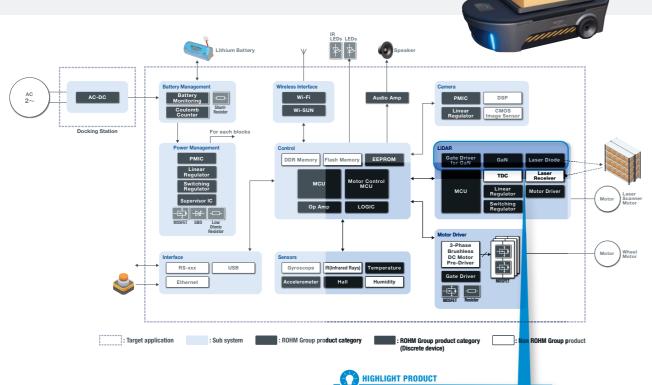
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AGV

AUTOMATED GUIDE VEHICLE

AGVs 🗈

As industrial automation progresses, AGVs are required to perform more accurate distance measurement and spatial awareness, increasing the demand for LiDAR (Light Detection and Ranging). ROHM contributes to the improvement of IoT technology for AGVs by combining wireless communication and sensors with long-range, high accuracy solutions for LiDAR using high-power laser diodes and GaN HEMTs.



Laser Diode, GaN HEMT: GaN HEMTs drive narrow emission laser diodes at high speeds, allowing LiDAR to achieve high accuracy at long distance



PRODUCT

Docking Station AC-DC Converters

Li-ion Battery pack Battery Monitoring D Coulomb Counter Shunt Resistors D

Power Supply

Switching Regulators D Linear Regulators D PMIC 🗈

Supervisor IC 🗈 MOSFETs 🗈 Schottky Barrier Diodes

Resistors 🗈

Wireless Interface Wi-SUN 🗈

LiDAR MCUs 🗈 Laser Diodes D Switching Regulators D

Sensors

Hall 🗈

Magnetic 🗈

Temperature 🗈

Accelerometer D

Linear Regulators D GaN HEMT Motor Drivers Gate Driver for GaN

Camera

PMIC 🗈 Linear Regulators D Control MCUs 🗈

EEPROMs 🗈 Standard Logic 🗈 Operational Amplifiers D IR LEDs D

Comparators

Mortor Drive

Gate Drivers MOSFETs 🗈

Resistors 🗈

Audio Amp 🗈 LEDs 🗈

■ ROHM starts Production of 150V GaN HEMTs: Featuring Breakthrough 8V Withstand Gate Voltage 📴 ■ 75W High Power Output Laser Diode for LiDAR D

REFLD002

Laser Driver Reference Design with GaN HEMT EcoGaN™ for High-Resolution LiDAR

The range of uses for LiDAR (Light Detection and Ranging) sensors is expanding to include not only autonomous driving, but also applications in the industrial and infrastructure fields. LiDAR sensors require longer sensing distances and higher resolution, so in addition to improving the characteristics of the laser diode, it is necessary to drive the laser diode at higher speeds and power. To meet these needs, ROHM offers the RLD90QZWx series of 905nm high power narrow emission laser diodes.



Reference designs are available that combine next-generation GaN HEMTs (EcoGaN™) capable of high-speed drive with high-speed gate drivers for GaN devices that contribute to improved LiDAR sensor characteristics.

Specifications

Refe	erence Design Part No.	REFLD002-1	REFLD002-2					
	Design Brief	REFLD002 Board Overview D						
	Board Part No.	S WAVE B-01	R WAVE B-01					
	Circuit Type	Square wave	Resonant					
Input Vo	Itage 1 (Laser Diode Drive)	up to 60V	up to 120V					
Input	Voltage 2 (Gate Driver)	5V						
	Laser Power	TBD						
S	witching Frequency	0.1 to 0.5kHz	0.1 to 100kHz					
	Laser Diodes	RLD90QZW8	RLD90QZW3 ▶					
	EcoGaN™	GNE1040TB □						
Onboard Devices	Gate Driver	BD2311NVX-C						
2071000	Reverse Current Protection Diode	RF05VAM2S □						
	Shunt Resistors	LTR10 s	series 📴					

Features

- Enables high-speed driving of laser diodes key devices in LiDAR applications
- Next-generation EcoGaN™ devices
- High-speed gate driver for GaN HEMTs (BD2311NVX-C)
- 2 circuit types: square wave/resonant

Application Examples

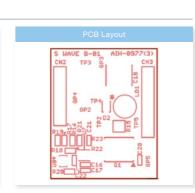
■ Automotive LiDAR ▶

■ Industrial LiDAR 🗈

■ Robot Vacuum Cleaner 🕒 🕒 AGV 🕒

Design Data e.g.: REFLD002-1 Square Wave Circuit







EcoGaN™ is a trademark or registered trademark of ROHM Co., Ltd.



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PROGRAMMABLE LOGIC

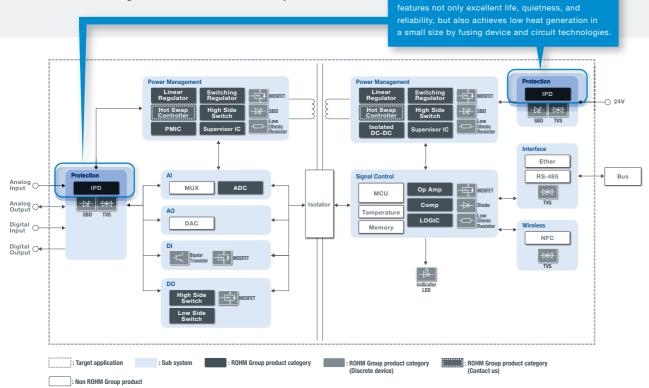
PLC 🗈

Control devices that act as the 'brains' of factory automation, PLCs are essential components for high reliability long-life application designs.

ROHM provides power semiconductors and power supply ICs for industrial power systems along with Intelligent

Power Devices (Smart Power Switches) that incorporate protection functions. High reliability solutions centered on high-voltage products improve application performance while extending the robustness and lifetime of systems.

HIGHLIGHT PRODUCT Intelligent Power Device: A protection element that features not only excellent life, quietness, and iability, but also achieves low heat generation in small size by fusing device and circuit technologi



PLC (Programmable Logic Controller) - Power Supply U

PRODUCT

Smart High Side Switch ICs (IPDs) Schottky Barrier Diodes D Transient Voltage Suppressor Diodes

Power Management

DC-DC Converter ICs Linear Regulators D PMIC 🗈 Supervisor IC 🗈 Smart High Side Switch ICs (IPDs)

Switching Regulators (Isolated type) Hot Swap Controller MOSFETs 🗈 Schottky Barrier Diodes 🗈

Resistors 🗈

Functional (AI, AO, DI, DO)

MOSFETs 🗈 Bipolar Transistors D A/D Converters

Smart High Side Switch ICs (IPDs) Smart Low Side Switch ICs (IPDs)

Signal Control

Serial EEPROMs D

Standard Logic D

Comparators D

Operational Amplifiers D

MCUs 🗈

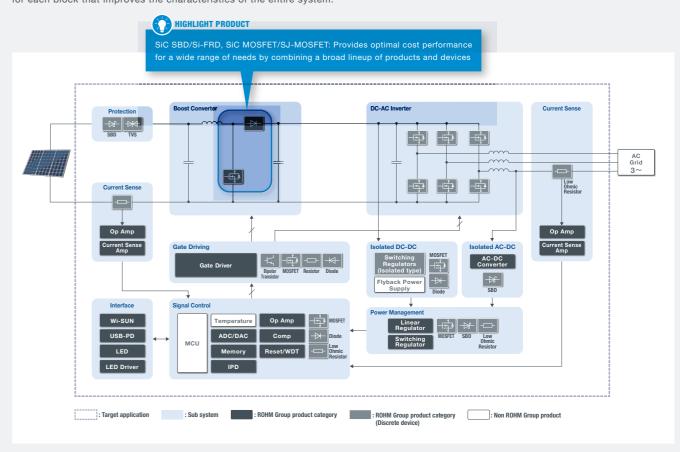
Transient Voltage Suppressor Diodes D

■ New Compact Intelligent (Smart) Low Side Switches: Reduced Power Loss and Safer Operation Using Proprietary TDACC™ Circuit and Device Technology [5]

SOLAR INVERTER

Solar Power Inverters (PV Inverters)

The use of renewable energy is becoming more active as the demand for photovoltaic power generation systems increases to achieve a low-carbon society. ROHM proposes power solutions centered on power semiconductors to efficiently transmit electricity generated from sunlight to the power grid. Whether configuring a circuit for boosting unstable DC voltage generated from solar power or converting it to AC power with the desired voltage and frequency using a DC-AC inverter, we offer a lineup of optimized components for each block that improves the characteristics of the entire system.



PRODUCT

Boost Converter SiC IGBT 📴

SJ-MOSFETs 🗈

SiC 🖪 IGBT 🗈 SJ-MOSFETs D

DC-AC Inverter

Gate Driver Isolated Gate Drivers D IGBT/MOSFET High/

Isolated DC-DC

Isolated DC-DC MOSFETs 🗈 Diodes 🗈

Isolated AC-DC AC-DC Converters

Schottky Barrier Diodes D **Current Sense**

Low Offset OpAmps D

Current Detection Resistors Current Sense Amplifiers

Low Side Gate Drivers

Power Management

Switching Regulators D Linear Regulators D Schottky Barrier Diodes D

MOSFETs 🗈 Resistors 🗈

Interface USB Power Delivery

LEDs 🗈 LED Drivers

Wireless communication D

Protection

Schottky Barrier Diodes 🗈 Transient Voltage Suppressor Diodes 🗈

Signal Control/General Purpose

FFPROMs D Operational Amplifiers D Comparators D

RESET ICs D D/A Converters MOSFETs 🗈

Diodes 🗈 Current Detection Resistors 🗈

Resistors D

■ PV Inverters D

■ New 4th Gen Fast Recovery Diodes Deliver Low Loss Performance Together with Ultra-Low Noise Characteristics 📴 ■ 600V Super Junction MOSFETs Deliver Class-Leading Low ON Resistance Along with the Industry's Fastest Reverse Recovery Time 🗈

*ROHM Friday, March 18, 2022 study

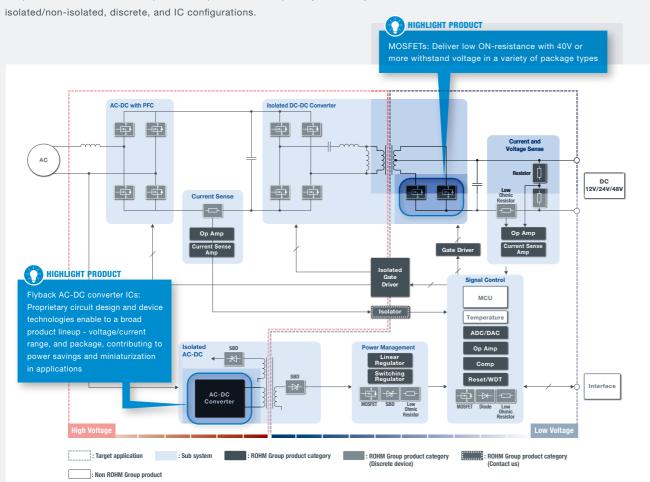
AC-DC CONVERTER

Industrial AC-DC Converters

In addition to the main power supply block, industrial AC-DC converters are required in auxiliary power circuits to provide power supply voltages for multiple control systems configured in a variety of topologies.

ROHM offers a broad lineup of semiconductor devices, ICs, and modules for a wide range of industrial power supply equipment.

We provide solutions that can optimize the performance of primary/secondary,



PRODUCT

AC-DC with PFC SiC 🗈

> Fast Recovery Diodes D SJ-MOSFETs 🗈

Isolated DC-DC Converter SiC MOSFETs 🗈

SJ-MOSFETs 🗈 MOSFETs(40V) MOSFETs(100V)

Gate Driver

Isolated Gate Drivers IGBT/MOSFET High/Low Side Gate Drivers D

Voltage and Current Sense

Current Detection Resistors Current Sense Amplifiers 🗈 Low Offset OpAmps D High Voltage Resistors

Linear Regulators D Schottky Barrier Diodes D MOSFETs 🗈 Resistors 🗈

Power Management

Switching Regulators D

Isolated AC-DC

AC-DC Converters Schottky Barrier Diodes 🗈

Signal Control/General Purpose

EEPROMs 🗈 Operational Amplifiers 🗈

Comparators D RESET ICs D

A/D Converters D/A Converters

MOSFETs D Diodes 🗈

Current Detection Resistors Resistors 🗈

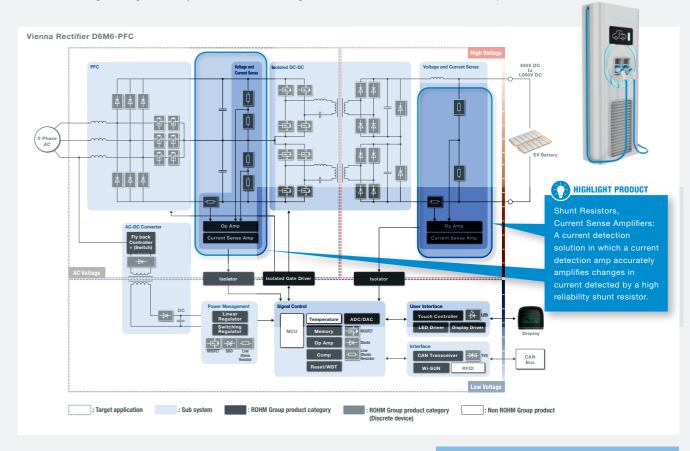
■ Industrial Power Converters/SMPS [5]

■ ROHM's Latest Generation Dual MOSFETs Deliver Class-Leading Low ON Resistance

XEV CHARGING STATION

EV Charging Stations

Fast charging technology at charging stations is quickly becoming indispensable for enhancing the convenience of EVs. To achieve this, high efficiency, high-frequency switching is necessary to reduce the size and weight of devices for rapid charging. ROHM contributes to even greater efficiency by providing power solutions such as driver ICs and power semiconductors centered on SiC devices along with high accuracy current detection using shunt resistors and current detection amps.





Wireless communication

Transient Voltage Suppressor Diodes D

CAN Transceivers

Interface

PRODUCT

AC-DC with PFC

Fast Recovery Diodes D SJ-MOSFETs 🗈

Isolated DC-DC Converter SiC MOSFETs D

SJ-MOSFETs D MOSFETs(40V) MOSFETs(100V)

Isolated Gate Driver

Isolated Gate Drivers

Voltage and Current Sense

Current Detection Resistors Current Sense Amplifiers Low Offset OpAmps D High Voltage Resistors D

Isolated AC-DC AC-DC Converters

Power Management Switching Regulators Linear Regulators D

Schottky Barrier Diodes D

Schottky Barrier Diodes 🗈 MOSFETs D

Resistors 🗈

User Interface

LEDs 🗈 LED Drivers(LCD Back light) Display Drivers

Signal Control/General Purpose

EEPROMs D Operational Amplifiers D Comparators 🗈 RESET ICs D A/D Converters D D/A Converters

MOSFETs 🗈 Diodes 🗈

Current Detection Resistors D Resistors D

= The Industry's Highest Rated Power (1W) Shunt Resistors in the 0508 Size Contributes to Greater Miniaturization in a Variety of Applications 📴 ■ ROHM's New ±1% Accuracy Current Sense Amplifier ICs Reduce Mounting Area by Approx. 46% Over Conventional Configurations 🗈

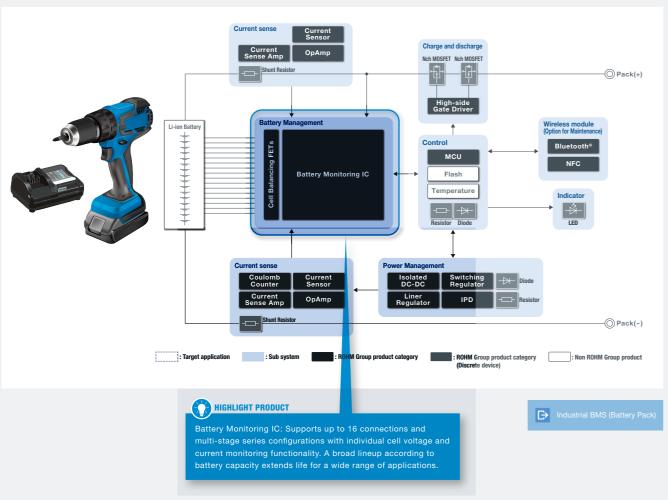
■ EV Charging Stations 🗈

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BATTERY MANAGEMENT SYSTEM

Industrial BMS (Battery Pack)

In the industrial equipment field, li-ion batteries (LiB) are used in various applications, including UPS (Uninterruptible Power Supply) and robots, increasing the importance of Battery Management Systems (BMS) in order to make effective use of batteries. At the same time, to increase the capacity of LiBs it is necessary to construct a high voltage system by configuring battery cells in multiple series. A broad lineup optimized for battery packs in industrial equipment is offered, including battery monitoring ICs that support up to 16 connections and multi-stage series connections along with high-accuracy Coulomb counters for large currents, contributing to the configuration of high performance, high precision battery management systems.



PRODUCT

Current Sense
Current Sense Amp
OpAmp 🗈
Current Sensor 🗈

Coulomb Counter Shunt Resistor D

Power Management

IPDs 🗈 Diodes 🗈 Resistors 🗈

Switching Regulators D Isolated DC-DC Linear Regulators D

Diodes 🗈

Battery Management

Battery Monitoring IC Cell Balancing FETs D

General-purpose MCUs(16bit) Resistors 🗈

Charge and Discharge Nch MOSFET D

High-side Gate Drivers Wireless Module

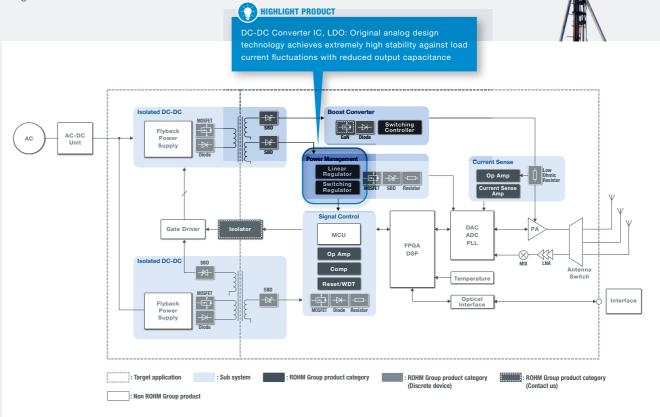
Bluetooth® Low Energy Modules D

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BASE STATION

Base Stations

5G and other high-speed communication base stations require high speed, high power systems to perform large-capacity signal processing for wireless demodulation and packet processing. At the same time, since many communication cells are used based on processing capacity and communication distance, they must be small enough to be installed virtually anywhere. In addition to power semiconductors, ROHM offers a lineup of compact, high voltage devices suitable for each block together with high efficiency power supply ICs that can reduce the number of components, providing solutions that contribute to not only lower power consumption, but greater miniaturization as well.





PRODUCT

Boost Converter

Switching Controller

Power Management Switching Regulators

Linear Regulators D Schottky Barrier Diodes

MOSFETs 🗈 Resistors 🗈

Current Sense

Current Detection Resistors Current Sense Amplifiers D Low Offset OpAmps D

Isolated DC-DC MOSFETs 🗈

Diodes 🗈

Auxiliary Isolated DC-DC Isolated DC-DC

MOSFETs 🗈 Diodes 🗈

Signal Control/General Purpose

EEPROMs 🗈

Operational Amplifiers D

Comparators 🗈 RESET ICs 🗈

D/A Converters D

MOSFETs 🗈

Diodes 🗈

Current Detection Resistors

Resistors D

■ New Automotive LDO Regulators: Stable Operation at Nanoscale Output Capacitance [5] ■ New DC-DC Converter IC for ADAS Achieves Best-in-Class-Leading Stable Operation [5]

21 ROHM Application Brochure for INDUSTRIAL

Indicator

LEDs 🗈

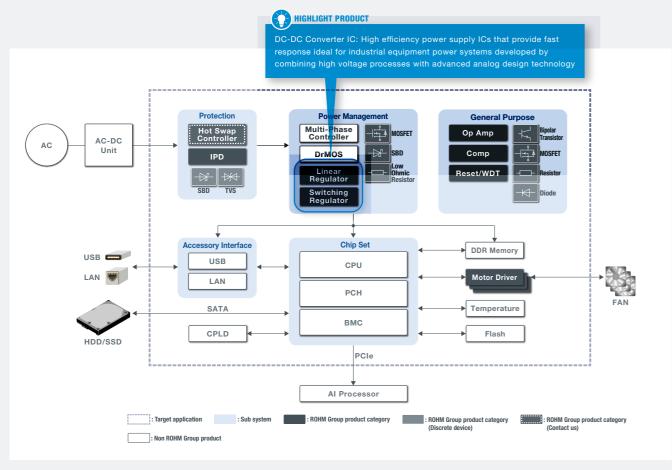
SERVER BOARD

Server CPU Board

The increased activity of cloud services and teleworking opportunities require that servers be faster and have greater capacity to handle more data. At the same time, however, increased power consumption resulting from higher server speeds and capacities are prompting the shift from conventional 12V distributed systems to centralized 48V systems for greater efficiency.

ROHM offers a lineup of DC-DC converter ICs that support both 12V distributed and 48V centralized systems.

Coil miniaturization through high-speed switching combined with high-speed response characteristics enable stable power supply under large current loads, contributing to lower power consumption and high reliability in server boards.



PRODUCT

Power Management Switching Regulators

> High Voltage Switching Regulators(>60V) ▶ Linear Regulators D

Schottky Barrier Diodes D

MOSFETs 🗈

Resistors D

Current Detection Resistors

Motor Driver

FAN Motor Drivers

Protection MOSFETs 🗈

IPDs 🗈

Schottky Barrier Diodes 🗈 Transient Voltage Suppressor Diodes

Hot Swap Controller

Signal Control/General Purpose

Operational Amplifiers D

Comparators 🗈

RESET ICs 🗈 MOSFETs 🗈

Diodes 🗈

Current Detection Resistors

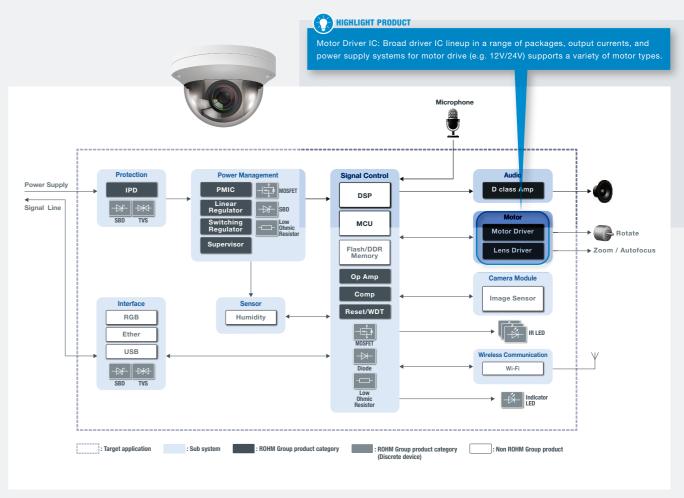
Resistors 🗈 Bipolar Transistors

■ New 80V Withstand 5A Output Power Supply ICs [BD9G500EFJ-LA, BD9F500QUZ] [5]

SURVEILLANCE CAMERA

Surveillance Cameras

Surveillance cameras provide greater safety and security by recording evidence while acting as a crime deterrent, and can even deliver notifications in the event of an emergency. In addition to semiconductor elements, power supply, and general-purpose ICs, ROHM offers a broad lineup of motor drivers for brush, stepper, and other motors that help reduce the number of design resources for surveillance cameras by providing the best solution based on application needs.



PRODUCT

Protection
IPDs (Smart Low Side & High Side Switch ICs)
Transient Voltage Suppressor Diodes ▶
Schottky Barrier Diodes [

Power Management DC-DC Converter ICs 🗈 Linear Regulators D Supervisor IC MOSFETs 🗈 Schottky Barrier Diodes D

Resistors D

Signal Control Operational Amplifiers D Comparators D MOSFETs 🗈 Diodes D Resistors D

Infrared LEDs D

LEDs 🗈

Lens Drivers D

Motor Drive ODC Brush Motor Drivers Transient Voltage Suppressor Diodes D Stepper Motor Drivers D Schottky Barrier Diodes 🗈

Class D Speaker

Amplifiers D

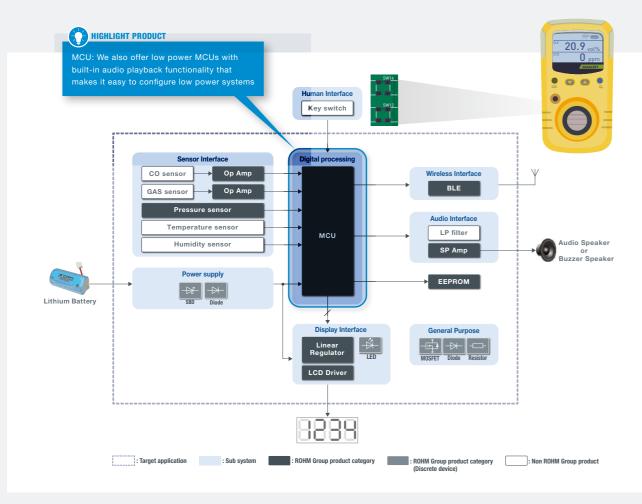
GAS LEAK ALARM

Gas Leak Detectors D

As devices that issue an alarm when detecting hazardous gases such as fuel leaks and carbon monoxide (CO) generated from incomplete combustion, gas leak detectors require high accuracy and reliability to ensure worry-free operation.

A human-friendly interface is also needed to provide voice notification of alarm information for storing data through communication functions to predict abnormalities.

ROHM contributes to safer living by offering everything from passive components to semiconductor elements, ICs, and modules that can achieve safety functions in equipment, with a focus on low-power MCUs and wireless communication technologies.



Gas leak alarm (Industrial use, handy ty

PRODUCT

Sensor Interface
Operational Amplifiers 🗈
Pressure Sensors D
Digital Processing

General-purpose MCUs(16bit) Speech Playback MCU 🗈 EEPROMs 🗈

Wireless Interface Bluetooth® Low Energy Module D Audio Interface Speaker Amp

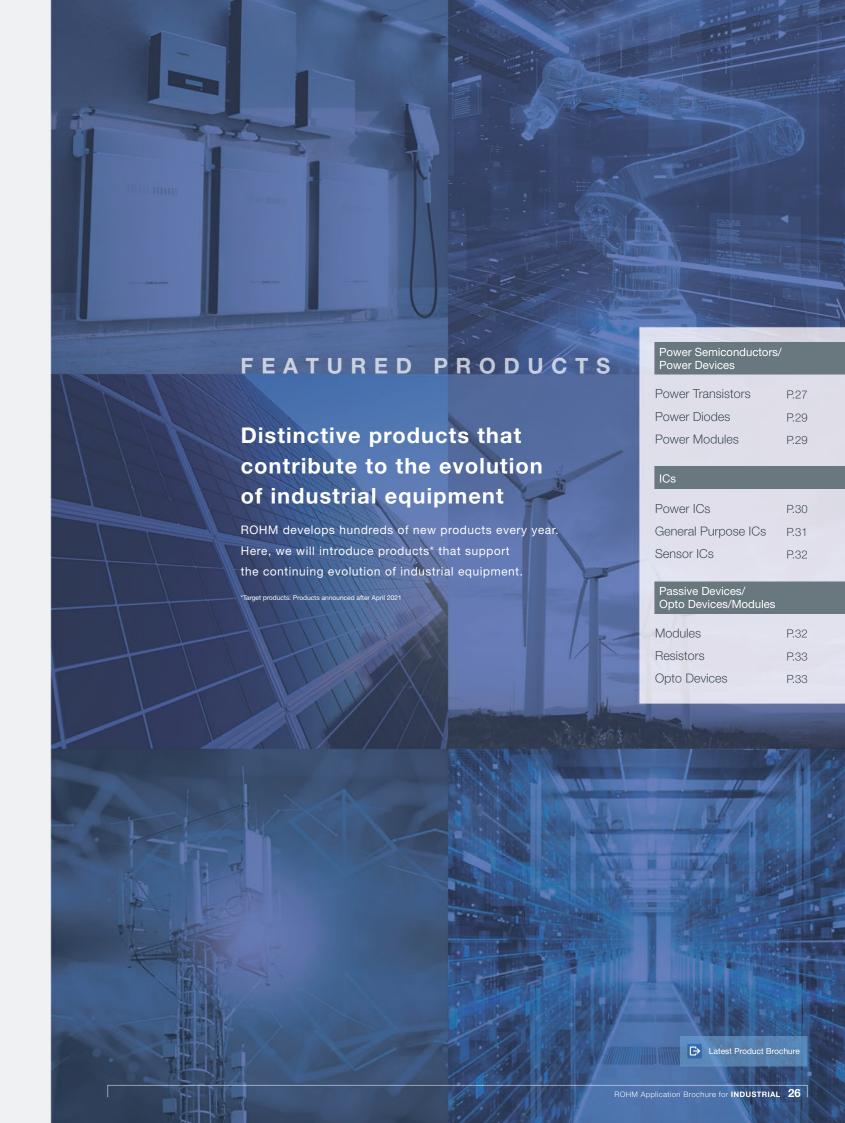
Power Supply Schottky Barrier Diodes D Diodes 🗈

> Display Interface Linear Regulators LEDs 🗈 LCD Drivers

General Purpose MOSFETs 🗈

Diodes 🗈 Resistors D

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Power Semiconductors/Power Devices

In the power device field, ROHM is strongly committed to the development of not only Si-based transistors and diodes, but also devices that use new materials such as SiC, as well as products that incorporate various structures, packages, and modularization. ROHM can provide a wide range of solutions to meet different power supply and motor drive needs, including ICs (control/drive ICs) that maximize the performance of power devices.

Power Transistors

4th Gen SiC MOSFETs

As the first supplier in the world to begin mass production of * SiC MOSFETs in 2010, ROHM continues to develop industry-leading SiC power device technologies. Among these are ROHM's latest 4th Gen SiC MOSFETs that deliver improved short-circuit withstand time along with the industry's lowest ON-resistance, making it possible to contribute to greater miniaturization and lower power consumption in a variety of applications, including inverters and switching power supplies.

Part No.	Polarity	V _{DSS}	I _D	P _D (W)	R _{DS (on)} Typ (mΩ)		lg (nC)	Package	
Part No.	(ch)	(V)	(A)	(T _c =25°C)	V _{GS} =18V	V _{GS} =18V	Drive Voltage (V)	Package	
SCT4013DE			105	312	13	170	15 to 18		
SCT4026DE		750	56	176	26	94	15 to 18		
SCT4045DE			34 115 45	45	63	15 to 18	TO-247		
SCT4018KE	N		81	312	18	170	15 to 18	(TO-247N)	
SCT4036KE		1,200	43	176	36	91	15 to 18		
SCT4062KE	1		26	115	62	64	15 to 18		
SCT4013DR			105	312	13	170	15 to 18		
SCT4026DR		750	56	176	26	94	15 to 18	_	
SCT4045DR			34	115	45	63	15 to 18	TO-247-4L	
SCT4018KR	N		81	312	18	170	15 to 18	⟨C15⟩	
SCT4036KR	1	1,200	43	176	36	91	15 to 18		
SCT4062KR			26	115	62	64	15 to 18		
SCT4013DW7			98	267	13	170	15 to 18		
SCT4026DW7		750	51	150	26	94	15 to 18		
SCT4045DW7	1		31	93	45	63	15 to 18	TO 062 71	
SCT4018KW7	N		75	267	18	170	15 to 18	TO-263-7L	
SCT4036KW7		1,200	40	150	36	91	15 to 18		
SCT4062KW7			24	93	62	64	15 to 18		

Note: Indicates the JEDEC package notation. () denotes ROHM package type, $\langle \ \rangle$ indicates the packaging symbol.

■ IGBTs with Built-in SiC Schottky Barrier Diode (Hybrid IGBTs) RGWxx65C series

The RGWxx65C series of hybrid IGBT utilizes ROHM's low-loss SiC Schottky barrier diode as the IGBT's freewheeling diode, resulting in significantly lower ON switching loss vs conventional IGBTs.

Field Stop Trench	Field Stop Trench IGBTs														
Part No.	V _{CES}	Ic (A)		P□	V _{CE (sat)}		tsc Min	I _{F (Diode)} (A)		V _{F (Diode)}		Package		Internal Circuit Diagram	
Part No.	(V)	T _C =25°C	T _C =100°C	(W)	Typ (V) Ic (A) (µse		(µsec)	T _C =25°C	T _C =100°C	Typ (V) I _F (A)		Fackage		Internal Offcult Diagram	
RGW60TS65CHR		64	39	178	1.5	30	_	39	25	1.35	20		1	j	
RGW80TS65CHR	650	81	48	214	1.5	40	-	39	25	1.35	20	TO-247N		# 	
RGW00TS65CHR	1	96	58	254	1.5	50	_	39	25	1.35	20			7	

Note: Indicates the JEDEC package notation.

RGWxx65C series Featured Product Cata

600V Super Junction MOSFETs R60xxVNx/R60xxRNx series

The R60xxVNx series of PrestoMOS™ power MOSFETs leverages original technology to achieve the industry's fastest trr (as of March 2022) while reducing ON resistance (which is in a trade-off with trr) by up to 20% over general super junction MOSFETs, contributing to higher efficiency in applications. At the same time, this series features the lowest noise of the PrestoMOSTM lineup, making it ideal for use in small motor equipment where noise is a concern.

Product No	-	Dolovitu	V _{DSS}		D (A)	R _{DS (a}	_{n)} (Ω)	Og Tup (pC)	ture Tires		
Part No.	Packing	Polarity (ch)	V _{DSS} (V)	Ι _D (A)	P _D (A) (T _C =25°C)	V _{GS} =	15V	Qg Typ (nC) V _{GS} =15V	trr Typ (ns)	Package	
raitivo.	code	(=,	(-)	()	(10 =1 0)	Тур	Max	103 121	()		
R6013VND3	TL1			13	131	0.250	0.300	21*	65		
R6009RND3	TL1	N	600	9	125	0.510	0.665	22.0	55	TO-252	
R6007RND3	TL1] "	000	7	96	0.730	0.940	17.5	50	(DPAK)	
R6004RND3	TL1			4	60	1.330	1.730	10.5	40		
☆R6055VNX3	C16			55	543	0.059	0.071	80*	112	C	
R6035VNX3	C16	N	600	35	348	0.095	0.114	50*	92	TO-220AB	
R6024VNX3	C16			24	245	0.127	0.153	38*	80		
☆R6055VNX	C7 G			23	99	0.059	0.071	80*	112		
R6035VNX	C7 G			17	81	0.095	0.114	50*	92		
R6024VNX	C7 G	N	600	13	70	0.127	0.153	38*	80	(TO-220FM) (TO-220FP)	
R6018VNX	C7 G			10	61	0.170	0.204	27*	68	(10 22011)	
R6013VNX	C7 G			8	54	0.250	0.300	21*	65		
☆R60A4VNZ4	C13			140	1,388	0.022	0.027	195*	167		
R6077VNZ4	C13	N	600	77	781	0.042	0.051	108*	125	TO-247AD (TO-247)	
R6055VNZ4	C13			55	543	0.059	0.071	80*	112	'	
R6077VNZ	C17	N	600	29	113	0.042	0.051	108*	125	(TO 2DE)	
R6055VNZ	C17	IN	600	23	99	0.059	0.071	80*	112	(TO-3PF)	

Note: Indicates the JEDEC package notation. (): ROHM Package, (): GENERAL Code.

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*V_{GS}=10V ☆:Under Development R60xxVNx series with Built-in High-Speed Diode (PrestoMOS™ R60xxYNx Low ON Resistance series Featured Product Catalog

R60xxRNx series Low Noise Type (PrestoMOS™) Featured Product Catalo

40V/60V Withstand Dual MOSFETs QH8Mx5/SH8Mx5 series (Nch+Pch) QH8Kxx/SH8Kxx series (Nch+Nch)

ROHM's dual MOSFETs pursue ON resistance performance in both Nch and Pch elements, combining two elements in a single package. This helps reduce design resources for motor and other applications.

Product No.			.,		5 446		R _{DS (on}	₀ (mΩ)	0 (0)						
		Polarity (ch)	V _{DSS} (V)	(A)	P _D (W) (T _a =25°C)	V _{GS} =	=10V V ₀		4.5V	Qg (nC) V _{GS} =4.5V	Package				
Part No.	code	(011)	(*)	(/-)	(1a-200)	Тур	Max	Тур	Max	VGS-4.5V					
QH8KB6	TCR		40	8	1.5	13.7	17.7	16.4	27	5.0					
QH8KB5	TCR	N+N	40	7.5*1	1.5	34	44	44	74	1.8	1				
QH8KC6	TCR	IN+IN	60	5.5	1.5	23	30	31	44	3.9	(TSMT8)				
QH8KC5	TCR]	60	3	1.5	70	90	100	140	1.7	3028 size				
QH8MB5	TCR		40	4.5	1.5	34	44	44	74	1.8					
QTIONIDO	1011	N+P	-40	-5	1.5	33	41	41	51	9.0					
QH8MC5	TCR	'**	60	3	1.5	70	90	100	140	1.7	İ				
OHOKBO	TD 4		-60	-3.5	1.5	71	91	79	101	8.5					
SH8KB6	TB1		40	8.5	2	14.9	19.4	18.2	26	5.0					
SH8KB7	TB1	N+N	40	13.5	2	6.5	8.4	7.5	10.5	13					
SH8KC6	TB1	INTIN	60	6.5	2	25	32	33	46	3.9	(SOP8)				
SH8KC7	TB1					60	10.5	2	9.5	12.4	12.3	17.2	10.8	5060	
SH8MB5	TB1		40	8.5	2	14.9	19.4	18.2	26	5	size	333			
SHOWIDS	IDI	N+P	-40	-40 -8.5		13.9	16.8	16.5	21	25		~			
SH8MC5	TD1	IN+P	60	6.5	0	25	32	33	46	3.9					
SHOWICO	TB1		-60	-7	2	27	33	29	37	23					

Note 1: () denotes ROHM package type.

Note2:*1 PW≤1s

Nch+Pch Dual MOSFETs (QH8Mx5/SH8Mx5 series), Nch+Nch MOSFETs (QH8Kxx/SH8Kxx series) Featured Product Cata

FEATURED PRODUCTS

Power Modules

Power Diodes

■ 650V Fast Recovery Diodes RFL Series (Low V_F Type) RFS series (High-Speed trr Type)

This series improves both V_F and trr performance (important diode characteristics in a trade-off relationship) over the previous generation.

Two types of devices are available to meet the needs of power supply circuits for different applications.

650V Power Fas	650V Power Fast Recovery Diodes															
Produ		Absolute	Maximum	Ratings (TC=25°C)		Electr	ical Char	acteristic			Equivalent				
Part No.	Grade code	Packing code	V _{RM} (V)	V _R (V)	I ₀ (A)	I _{FSM} (A) 60Hz.1 ℃	V _F (V) Max	I _F (A)	I _R (μΑ) Max	V _R (V)	trr (ns) Max	I _F (A)	I _R (A)	Package	Circuit Diagram	
RFL30TZ6S	G	C13			30	200	1.5	30	5	650	55	0.5	1	2.0		
RFS30TZ6S	G	C13	650	CEO.	650	30	160	2.3	30	5	650	35	0.5	1	TO-247-2L	o → N → ○
RFL60TZ6S	G	C13		650	60	320	1.5	60	10	650	75	0.5	1	(TO-247GE-2L)	0 4 0	
RFS60TZ6S	G	C13			60	250	2.3	60	10	650	55	0.5	1			
☆RFL30TS6D	G	C13			30*1	100*2	1.5	15	5	650	45	0.5	1			
☆RFS30TS6D	G	C13	650	050	30*1	80*2	2.3	15	5	650	30	0.5	1	TO-247-3L	<u>→</u>	
☆RFL60TS6D	G	C13		650	650	60*1	180*2	1.5	30	5	650	55	0.5	1	(TO-247GE-3L)	
☆RFS60TS6D	G	C13			60*1	150*2	2.3	30	5	650	35	0.5	1			

^{*1:} The average output current per element is Io (with one element) or 1/2 Io (with 2 elements). *2: Standard per element.

Note: Indicates the JEDEC package notation. () denotes ROHM package type.

☆: Under Development



Compact High Reliability PMDE Package Schottky Barrier Diodes

The PMDE package (2.5mm×1.3mm), which not only achieves the same characteristics in a smaller size vs the general SOD123FL (3.5mm×1.6mm), but also provides 1.4x higher mounting strength, is being commercialized for various diodes.

PMDE Package	Medium	Powe	r Sch	ottky	Barri	er Dioc	les					
Product	No.		Absolut	e Maximu	m Ratings	s (TC=25°C)	Ele	ctrical Charac	teristics (Tj=	25°C)		
Part No.	Grade code	Packing code	V _{RM} (V)	V _R (V)	I _o (A)	I _{FSM} (A) 60Hz.1∼	V _F (V) Max	I _F (A)	I _R (mA) Max	V _R (V)	Package	Equivalent Circuit Diagram
High Efficiency-Low	/ I _R Type											
RBLQ2VWM10	*	TR	100	100	2	30	0.77	2	0.01	100		
Low V _F Type												
RBR1VWM30A		TR	30	30	1	30	0.48	1	0.05	30		
RBR2VWM30A		TR	30	30	2	30	0.53	2	0.05	30		
RBR1VWM40A	*	TR	40	40	1	20	0.52	1	0.05	40		
RBR2VWM40A		TR	40	40	2	20	0.62	2	0.05	40		
RBR1VWM60A		TR	60	60	1	20	0.53	1	0.075	60		
RBR2VWM60A		TR	60	60	2	20	0.65	2	0.075	60		
Ultra-Low I _R Type											(PMDE)	<u></u>
RB168VWM-30		TR	30	30	1	30	0.69	1	0.0006	30		
RB068VWM-30		TR	30	30	2	30	0.75	2	0.0006	30		
RB168VWM-40		TR	40	40	1	30	0.69	1	0.0005	40		
RB068VWM-40		TR	40	40	2	30	0.79	2	0.0005	40		
RB168VWM-60	*	TR	60	60	1	30	0.76	1	0.0005	60		
RB068VWM-60	_ ^	TR	60	60	2	30	0.84	2	0.0005	60		
RB168VWM100		TR	100	100	1	25	0.84	1	0.0003	100		
RB068VWM100		TR	100	100	2	25	0.94	2	0.0003	100		
RB168VWM150		TR	150	150	1	25	0.89	1	0.001	150		
RB068VWM150		TR	150	150	2	25	0.96	2	0.001	150		

^{*}The Grade code is left blank

Note 1: () denotes ROHM package type.



Power Modules

600V IGBT-IPMs BM6437x series

Optimizing the built-in IGBT and fast recovery diode allows the BM6437x series to decrease radiated noise by more than 6dB over standard products. What's more, utilizing low-loss IGBTs results in class-leading low loss.

600V IGBT-IPMs	S							
Part No.	Power Device	V _{CES}	lc	PWM Input Frequency	Isolation Voltage*1	Thermal Protect	ction Function*2	Dealessa
Part No.	Power Device	(V)	(A)	(kHz)	(Vrms)	TSD	VOT	Package
BM64374S-VA			15			~	~	HSDIP25
BM64375S-VA	IODT	600	20	to 00	1 500	~	~	HSDIP25
BM64377S-VA	IGBT	600	30	- up to 20	1,500	~	~	HSDIP25
BM64378S-VA			35			~	V	HSDIP25

^{*1:} Supports 2,500Vrms when using a convex heat sink at AC60Hz for 1min *2: TSD (Thermal Shutdown), VOT (Analog Temperature Output)



ICs

Since the development of its first ICs in the 70's, ROHM has established and refined a three-pronged development system that thoroughly aligns analog technologies covering circuit design, layout, and processes. These technologies are utilized in the development of high value-added products centered on control and driver ICs that can maximize the performance of power supply ICs and power devices.

Power ICs

AC-DC Converters with Built-in 1,700V SiC MOSFET BM2SC12xFP2-LBZ series

The BM2SC12xFP2-LBZ series combines a SiC MOSFET for unprecedented power saving performance with control circuitry optimized for auxiliary industrial power supplies in a single package. This resolves many of the design issues plaguing discrete solutions, making it easy to develop power-saving AC-DC converters.

AC-DC Convert	ers with	Built-in 1,700	OV Si	C MOSF	ET					
Part No.	Supply Voltage (V)	SiC MOSFET V _{DS} (Max) (V)	Control Method	Maximum Frequency (kHz)	ON Resistance (Ω)	OCP Exchange Function	V _{cc} OVP Protection	FB OLP Protection	ZT OVP Protection	Package
BM2SCQ121T-LBZ							Latch	Auto Restart		
BM2SCQ122T-LBZ	15 to 27.5	1.700	QR	120	1.12	1.12	Laten	Latch	Latch	TO220-6M
BM2SCQ123T-LBZ	15 10 27.5	1,700	Qh	120	2		Auto Restart	Auto Restart	Laich	10220-6WI
BM2SCQ124T-LBZ							Auto nestart	Latch		MA I
BM2SC121FP2-LBZ							Latch	Auto Restart		
BM2SC122FP2-LBZ	15 to 27.5	1 700	QR	120	1.12		Laten	Latch	Latch	TO263-7L
BM2SC123FP2-LBZ	15 to 27.5	1,700	Qn	120	1.12		Auto Restart	Auto Restart	Laten	TO263-7L
BM2SC124FP2-LBZ							Auto Restart	Latch		

Built-in SiC MOSFET AC-DC Converters Lea

FEATURED PRODUCTS

AC-DC Converter ICs with Built-in 730V Super Junction MOSFET BM2P06xMF-LBZ series

The BM2P06xMF-Z series of surface mount ICs combines ROHM's low-loss Super Junction MOSFETs with control circuitry in a single package, facilitating the development of 85V to 264V AC-DC converters that deliver high output power up to 45W.

AC-DC Convert	er ICs w	/ith B	uilt-ir	1 730\	/ Sup	er Jı	ınctio	n MC	SFE	Γ					
Part No.	Supply Voltage (V)	MOSFET Vos (Max) (V)	Control Method	Switching Frequency (kHz)	Frequency Reduction Function	Max Duty (%)	ON Resistance (Ω)	Peak Current (A)		Overcurrent Limiter (V)	Current Sense Resistor	Startup Current (mA)	Brownout	FB OLP Protection	Package
BM2P060LF-Z							0.7	21.0						1 -4-1-	
BM2P061LF-Z							1.0	12.0						Latch	
BM2P060MF-Z	11 to 60	730	PWM	65	~	75	0.7	21.0	~	~	Extrenal	15	~		SOP20A MANAGEMENT
BM2P061MF-Z							1.0	12.0						Auto Restart	1777
BM2P063MF-Z							3.0	4.0							

BM2P06xMF-Z series Featured Product Ca

■ 45V Withstand 150mA Output Nano CapTM LDO Regulators BD9xxN1 series

The BD9xxN1 series supports small output capacitances down to 100nF utilizing proprietary Nano Cap™ ultra-stable control technology,

ensuring extremely stable operation even when the input voltage or output load current fluctuates.

In addition to reducing the size of components and substrates, the number of design resources can be significantly reduced by enabling compatibility with a wide range of capacitors.

5V Withstand I	Low Iq 1	50mA (Output Na	no Cap	o™ LDO F	Regulat	ors				
T	Input		Output Voltage	Output	Input-Output	Circuit	Operating	Shutdown	Protection	Package	/Part No.
Туре	Voltage (V)	Voltage (V)	Accuracy (%)	Current (A)	Voltage Difference (V)	Current (µA)	Temperature (°C)	Switch	Circuits	HTSOP-J8	SSOP5
BD900N1		Variable								BD900N1EFJ-C	BD900N1G-C
BD933N1	3 to 42	3.3	3.3 ±2.0	0.15	0.5 (I _o =100mA)	28	T _j =-40 to +150	-	Over-Current/ Temperature	BD933N1EFJ-C	BD933N1G-C
BD950N1		5.0]							BD950N1EFJ-C	BD950N1G-C
BD900N1W		Variable								BD900N1WEFJ-C	BD900N1WG-
BD933N1W	3 to 42	3.3	3.3 ±2.0	0.15	0.5 (I ₀ =100mA)	28	T _j =-40 to +150		Over-Current/ Temperature	BD933N1WEFJ-C	BD933N1WG-
BD950N1W]	5.0			(10-10011111)		1100		remperature	BD950N1WEFJ-C	BD950N1WG-



FEATURED PRODUCTS

45V Withstand 50mA Output Compact Ultra-Low Quiescent Current LDO Regulators BD7xxL05G-C series

Despite its small size (2.9mm×2.8mm), the BD7xxL05G-C series achieves a Withstand voltage of 45V with low 6uA quiescent current, enabling suitability for a wide range of applications that require a small form factor, low power consumption, and constant operation.

45V Withstand L	ow Iq 50	mA Outp	ut LDO Re	gulators						
Part No.	Input Voltage (V)	Output Voltage (V)	Output Voltage Accuracy (%)	Output Current (A)	Input-Output Voltage Difference (V)	Circuit Current (µA)	Operating Temperature (°C)	Shutdown Switch	Protection Circuits	Package
BD725L05G-C	3.5 to 42.0	2.5			_					•
BD730L05G-C	3.5 to 42.0	3.0	±2	0.05	0.3 (I _o =50mA)	6	-40 to +125		Over-Current/	SSOP5
BD733L05G-C	3.8 to 42.0	3.3	==2	0.03	0.3 (I ₀ =30IIIA)		-40 t0 +125	_	Temperature	330F3
BD750L05G-C	5.6 to 42.0	5.0			0.35 (I _o =50mA)					



40V Low-Side IPDs (Smart Low-Side Switches) with Error Flag BV1LExxxEFJ-C/BM2LExxxFJ-C series

Both series provide the advantage of easy design through a circuit configuration that facilitates replacement of standalone mechanical relays and MOSFETs when placed in the lower (ground side) circuits of equipment to be controlled.

Low ON resistance together with heat suppression are enabled in a small size (difficult to achieve), contributing to significantly lower power loss and safer device operation.

Low-Side IPDs (Smart Low-Sid	e Switches) v	vith 40V Erro	or Flag					
Part No.	Supply Voltage (V)	V _{DS} Max (V)	ch	I _{ocp} Max (A)	ON Resistance (Typ) (mΩ)	TSD	Package		
BV1LE040EFJ-C		40		17.5	40				
BV1LE080EFJ-C	3.0 to 5.5	40	1	9.0	80		HTSOP-J8		
BV1LE160EFJ-C	3.0 to 5.5	40	'	5.0	160		111301-30		
BV1LE250EFJ-C		40		3.0	250	Self-restart			
BM2LE040FJ-C		40		17.5	40	Jen-restart			
BM2LE080FJ-C	3.0 to 5.5			9.0	80		SOP-J8		
BM2LE160FJ-C	3.0 (0 5.5	40	2	5.0	160		30F-00		
BM2LE250FJ-C		40		3.0	250				

BV1LExxxEFJ-C (1ch)/BM2LExxxFJ-C (2ch) series Featured Product Catalog

Gate Driver ICs for GaN HEMT (Single-channel) BD2311NVX-LB

The BD2311NVX-LB is a single-channel gate driver IC optimized for driving GaN HEMTs.

In addition to supporting narrow pulse high-speed switching required for GaN HEMTs, a built-in original overshoot suppression circuit ensures GaN reliability.

Gate Driver ICs	Gate Driver ICs for GaN HEMT (Single-channel)													
Dort No.	Part No. Supply Voltage Output Current Typ Delay Time Typ (ns) Minimum Input Pulse Width Typ Operating Temperature Package													
Part No.	(V)	(A)	Turn ON	Turn OFF	(ns)	(°C)	Package							
BD2311NVX-LB	4.5 to 5.5	+7/-5	0.65	0.70	1.25	-40 to +125	SSON06RX2020							
☆BD2311NVX-C	4.5 (0 5.5	+1/-5	0.05	0.70	1.25	-40 10 +125	33UNU0HX2U2U							

☆: Under Development

BD2311NVX-LB Featured Product Cata

General Purpose ICs

40V Window-Type Voltage Detector (Reset IC) BD48HW0G-C

The BD48HW0G-C achieves operating voltages up to 40V along with an ultra-high voltage detection accuracy of ±0.75% while minimizing current consumption to just 500nA. What's more, a flexible detection voltage enables use in a wide range of applications, from the low voltage region around MCUs to the high voltages used in industrial equipment power supplies.

Window-Type Vo	ltage D	etectors	(Rese	t ICs)						,		
Part No.	Operating Supply Voltage (V)	Detection Voltage Accuracy Ta=All Temperatures (%)	Dotootion	Low Voltage Detection (V)	Output Type	Circuit Current (nA)	Hysteresis Voltage (V)	"L" Outpu (m (V _{DS} =	A)	Reset Release Propagation Delay Time (ms)	Delay Time Accuracy (%)	Package
BD48HW0G-C	1.8 to 40	±0.75	1.277	1.277		500		2 or more	(V _{DD} =1.8V)			
BD48W00G-C		±2.5	1.2	1.2		3000				_	_	
BD52W01G-C			1.32	1.08								
BD52W02G-C			1.65	1.35	Open		V _{DET} ×0.01	1	2			SSOP6
BD52W03G-C	1.6 to 6.0	±5	1.98	1.62	Drain	300	V DETXU.UI	or more	or more	Variable	±50	SSOFU ST
BD52W04G-C		±5	2.75	2.25		300		(V _{DD} =1.6V)	(V _{DD} =2.4V)	variable	(All Temperature)	~
BD52W05G-C			3.63	2.97								
BD52W06G-C			5.5	4.5								



Sensor ICs

Compact Waterproof High Accuracy Barometric Pressure Sensor BM1390GLV-Z

The BM1390GLV delivers IPX8 waterproof performance in a compact size. At the same time, excellent temperature characteristics that suppress characteristics fluctuations due to stress enable high accuracy barometric pressure measurement even in environments with large temperature variations.

Compact Waterp	Compact Waterproof High Accuracy Barometric Pressure Sensor IC													
Part No. Supply Voltage (V) Barometric Pressure Range (hPa) Accuracy (hPa) Accuracy (hPa) I/F Operating Temperature (C) Waterproof Rating (mm)														
BM1390GLV-Z	1.7 to 3.6	300 to 1,300	±0.06	±1	I ² C	-40 to +85	~	RLGA10VG020T 2.0×2.0, H=Max 1.0						



FEATURED PRODUCTS

Current Sense Amps BD1421x-LA series

The BD1421x-LA series of amp ICs are specialized for current detection using shunt resistors. Integrating peripheral components reduces the number of external parts while optimizing the circuit, enabling high accuracy ±1% current detection over the entire temperature range when combined with a shunt resistor.

Current Sense A	mp IC	S						
Part No.	ch	Supply Voltage (V)	Current Consumption (µA)	Common-Mode Voltage(V)	Gain (V/V)	Current Sense Accuracy (%)	Operating Temperature (°C)	Package (mm)
BD14210G-LA	1	2.7 to 5.5	170	-0.2 to +26	20	±1 (Max)	-40 to +125	SSOP6 2.9×2.8, H=Max 1.25
☆BD14215FVJ-LA	2	2.7 to 5.5	310	-0.2 to +26	20	±1 (Max)	-40 to +125	TSSOP-B8J 3.0×4.9, H=Max 1.10



Passive Devices/Opto Devices/Modules

ROHM also develops resistors (a founding product) as well as opto devices and modules that incorporate various elements.

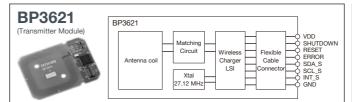
We continue to contribute to the evolution of industrial equipment by leveraging our strengths as a comprehensive semiconductor manufacturer to provide optimized solutions utilizing ICs and discrete components.

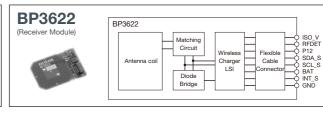
Modules

13.56MHz (NFC) Wireless Charger Modules BP3621 (Transmitter)/BP3622 (Receiver)

ROHM's 13.56MHz wireless charger is a board-integrated module with built-in antenna.

The optimized design significantly reduces the number of development resources required for antenna design and matching, making it easy to achieve wireless charging functionality while contributing to the design of compact, connectorless, water-and dust-proof enclosures required for wearables and IoT devices.





Wide Rangi	Wide Ranging 13.56MHz Wireless Charger Transmitter Module													
Part No.	Transmitter/ Receiver	Module Type	Module Size (mm)	Weight (g)	Supply Voltage (V)	Maximum Output Power (mW)	Charging Distance (d) (mm)	Operating Temperature (°C)	l/F					
BP3621	Power Transmitter	Wide Range type	35.0×26.0×1.5	0.80	4.5 to 5.5	_	10	–10 to +50	8pin, 0.5mm pitch, FPC connector					
Wide Rangi	Wide Ranging 13.56MHz Wireless Charger Receiver Module													
BP3622	Power Receiver	Wide Range type	24.0×17.0×1.5	0.38	_	200	10	-10 to +50	8pin, 0.5mm pitch, FPC connector					

FEATURED PRODUCTS

Resistors

■ Ultra-Low Ohmic High Power Metal Plate Shunt Resistors PSR series

The PSR series consists of high power ultra-low-ohmic metal plate shunt resistors ideal for current sensing applications. A full lineup of sizes and resistances are available, enabling high accuracy current detection in a wider range of applications.

Ultra-Low Ohmic High Power Metal Plate Shunt Resistors												
Part No.	Size Code	Resistance	Rated Power (W) (Ra	ated Terminal Temp)	Resistance	Temperature Coefficient	Rated Current	Operating Temp				
T dit 140.	mm (inch)	(mΩ)	Low Temperature Side	High Temperature Side	Tolerance	of Resistance (ppm/°C)	(A)	(°C)				
		☆ 0.2	12 (1	20°C)		150±50						
		0.3				0 to +150						
PSR100	6432 (2512)	0.5	8 (75°C)	4 (140°C)	F (±1%)	0 to +100	36 to 163					
Poniuu		1.0			F (±170)	0 to +100	200					
		2.0	6 (75°C)	4 (140°C)		0 to +50						
		3.0	4 (75°C)	3 (140°C)		0 to +50						
		0.1	15 (1	20°C)		100±50						
PSR330	6464 (2525)	0.5	8 (1	00°C)	F (±1%)	0 to +100	77 to 387					
		1.0	6 (1	00°C)		0 to +50						
PSR350	7.9×5.6 (3222)	0.27	12 (120°C)		F (±1%)	0 to +150	Up to 210					
		0.2	12 (75°C)	5 (130°C)		125±50						
	10×5.2 (3921)	0.3	10 (75°C)	5 (130°C)		0 to +100		-65 to +175				
PSR400		0.5	10 (75°C)	5 (130°C)	E (.10/)	0 to +100	40 to 244					
P3N400		1.0	8 (75°C)	5 (130°C)	F (±1%)	0 to +75	40 10 244					
		2.0	6 (75°C)	4 (115°C)		0 to +75						
		3.0	5 (70°C)	3 (115°C)		0 to +75						
		0.1	15 (75°C)	10 (120°C)		200±50						
PSR500		0.2	15 (75°C)	10 (120°C)		0 to +150						
		0.3	10 (75°C)	7 (120°C)		0 to +150						
	15×7.75 (5931)	0.4	10 (75°C)	7 (120°C)	F (±1%)	0 to +150	59 to 387					
		0.5	10 (75°C)	7 (120°C)		0 to +150						
		1.0	10 (75°C) 6 (120°C)			0 to +75						
		2.0	7 (70°C)	4 (115°C)		0 to +75						

*(+20°C to +175°C) ☆: Under Development



Opto Devices

■ 1608 Size Low Current Chip LEDs CSL1901 series

The CSL1901 series of LEDs reduces visual variations in brightness and color under low light conditions by matching element characteristics to provide light emission at 2mA. Compared to general products (at 2mA), brightness variations are reduced by half and color differences suppressed, minimizing design resources required for light emission adjustment while improving visibility in indicators.

1608 Size	1608 Size Low Current Chip LEDs																	
Package (mm)	Emitting Color	Part No.	Electrical-Optical Characteristics (T₃=25°C)									Absolute Maximum Ratings (T _a =25°C)						
			Emission Wavelength λ _D / Chromaticity (x,y)		Brightness I _V			Forward Voltage V _F		Reverse Current I _R		Permissible Forward Loss Current		Peak Forward Current	Forward Voltage	Operating Temp.	Storage Temp.	
			Typ (nm)	I _F (mA)	Min (mcd)	Typ (mcd)	Max (mcd)	I _F (mA)	Typ (V)	I _F (mA)	Max (μA)	V _R (V)	P _D (mW)	I _F (mA)	I _{FP} (mA)	V _F (V)	Topr (°C)	Tstg (°C)
	Red	CSL1901VW	630	2	1.6	4.8	6.3	2	1.8	2	10	5	44	20	100*1	5	-40 to +85	-40 to +100
		CSL1901UW	620	2	2.5	6	10	2	1.8	2	10	5	44	20	100*1	5	-40 to +85	-40 to +100
	Orange	CSL1901DW	605	2	6.3	9.4	25	2	1.8	2	10	5	44	20	100*1	5	-40 to +85	-40 to +100
ALC: N. LOW.	Yellow	CSL1901YW	590	2	6.3	9.4	25	2	1.8	2	10	5	44	20	100*1	5	-40 to +85	-40 to +100
1.6×0.8 (t=0.55)	Yellow Green	CSL1901MW	570	2	1	3	4	2	1.8	2	10	5	44	20	100*1	5	-40 to +85	-40 to +100

*1 Duty≤1/10, 1kHz

CSL1901 series Featured Product Catalogue

905nm Invisible Pulsed 120W High Power Laser Diode RLD90QZW8

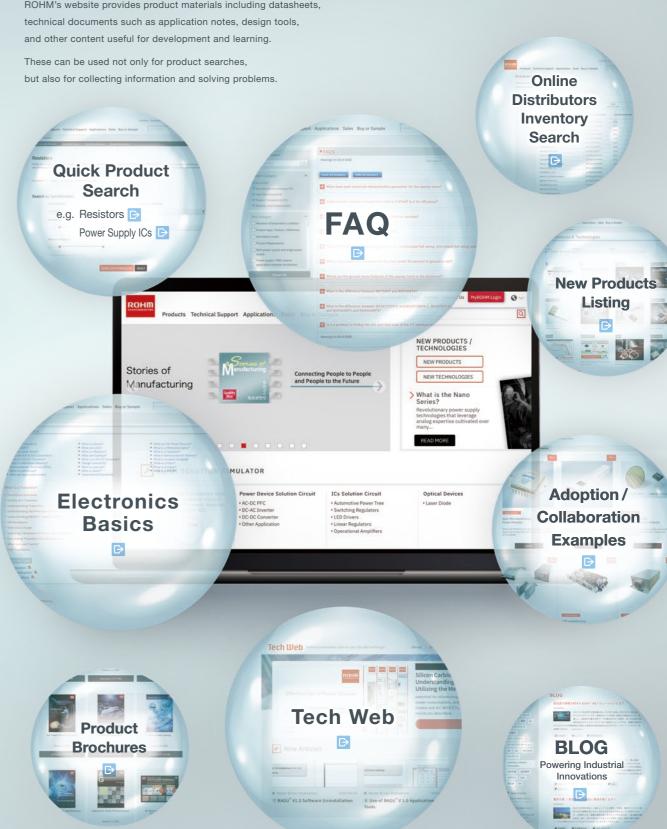
The RLD90QZW8 is a 120W infrared high power laser diode developed for distance measurement and spatial recognition applications such as LiDAR. Extremely low wavelength temperature dependence together with excellent luminous performance allow for high-definition, power-efficient, long-distance detection.

905nm Invisible	905nm Invisible Pulsed High Power Laser Diodes													
	Absolute Max. Ratings (Tc=25°C)						Elect	rical-Optical Cha		Equivalent				
Part No.	I _F (A)	P _o (W)	V _R (V)	Operating Temperature (°C)	I _F Conditions (A)	P _o (W)	V _F (V)	Vertical Beam Spread Angle θ ⊥ (deg)	Horizontal Beam Spread Angle θ // (deg)	Wavelength λ _P (nm)	Luminous Area (µm×µm)	Package	Circuit Diagram	
RLD90QZW8	46	145	10		38	120	13	20	11		270×10			
RLD90QZW3	28	90	2		23	75	11	25	12		225×10		(2)	
RLD90QZWD	13	3 40	2		12	35	11	25	13		100×10		(3)	
RLD90QZWB	11	25	2	-40 to	9	25	13	25	14	905	50×10	Ø5 0 OAN	<u></u>	
RLD90QZW5	9	25	2	+85	9	25	14	25	12	905	70×10	Φ5.6mm CAN	LD LD	
RLD90QZWC	11	30	2		9	25	11	25	13		70×10		(1)	
RLD90QZWJ	9	25	2		9	25	15	20	14		50×10			
RLD90QZWA	6	17	2		5	15	13	20	14		35×10			

RLD90QZW8 Featured Product Catalogue

ROHM Website

ROHM's website provides product materials including datasheets,



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